

# **PMZ1200UPEYL** Datasheet



DiGi Electronics Part Number	PMZ1200UPEYL-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	PMZ1200UPEYL
Description	MOSFET P-CH 30V 410MA DFN1006-3
Detailed Description	P-Channel 30 V 410mA (Ta) 310mW (Ta), 1.67W (Tc ) Surface Mount SOT-883

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# Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMZ1200UPEYL	Nexperia USA Inc.
Series:	Product Status:
-	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	410mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
1.5V, 4.5V	1.40hm @ 410mA, 4.5V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
950mV @ 250µA	1.2 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±8V	43.2 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	310mW (Ta), 1.67W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-883	SC-101, SOT-883
Base Product Number:	
PMZ1200	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



# PMZ1200UPE

30 V, P-channel Trench MOSFET 25 March 2015

Product data sheet

### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD package: 1.0 x 0.6 x 0.48 mm

### 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

able 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-30	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	[1]	-	-	-410	mA
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 25 °C		-	1.2	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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# **PMZ1200UPE**

30 V, P-channel Trench MOSFET

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D
2	S	source	2 2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S 017aaa259

# 6. Ordering information

Table 3. Ordering information				
Type number Package				
	Name	Description	Version	
PMZ1200UPE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883	

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMZ1200UPE	ZL

### **PMZ1200UPE**

30 V, P-channel Trench MOSFET

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-30	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-410	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-260	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-1.7	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T <sub>sp</sub> = 25 °C		-	1670	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-410	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

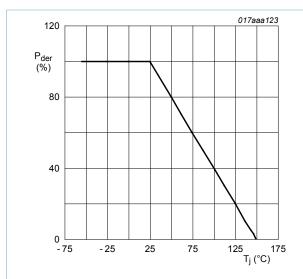
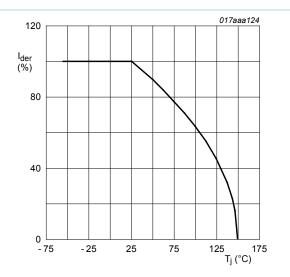


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

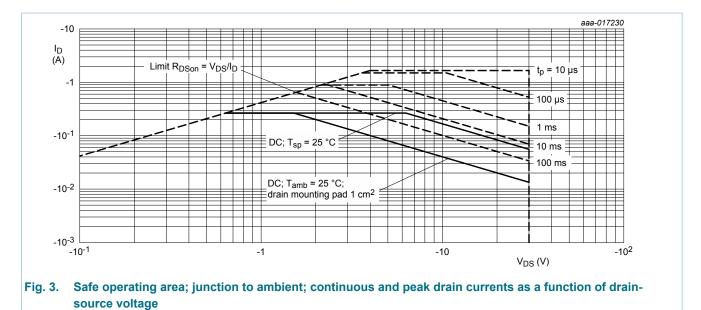




$$I_{der} = rac{I_D}{I_{D(25^\circ C)}} imes 100 \%$$

# PMZ1200UPE

#### 30 V, P-channel Trench MOSFET



## 9. Thermal characteristics

#### Table 6. Thermal characteristics

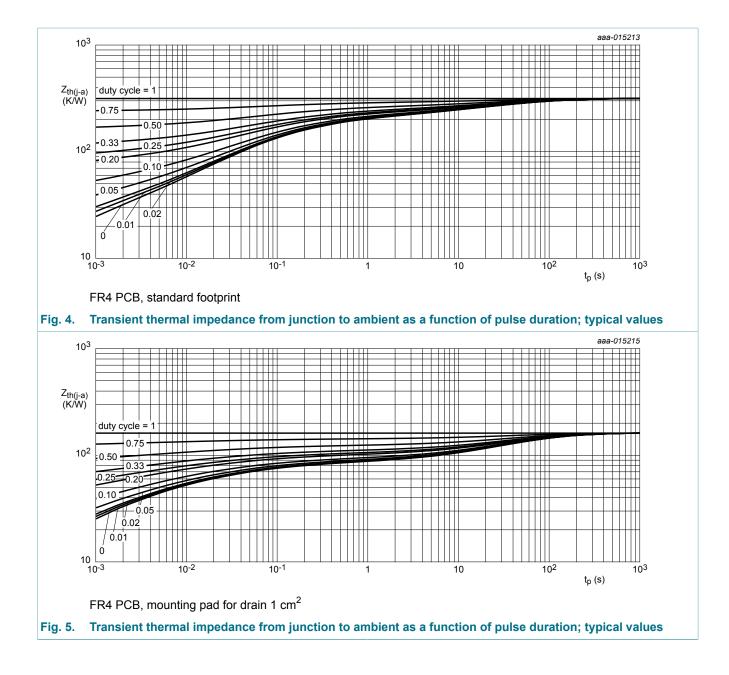
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	-	[1]	-	350	405	K/W	
		[2]	-	270	310	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	65	75	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

# PMZ1200UPE

#### 30 V, P-channel Trench MOSFET



# PMZ1200UPE

30 V, P-channel Trench MOSFET

### **10. Characteristics**

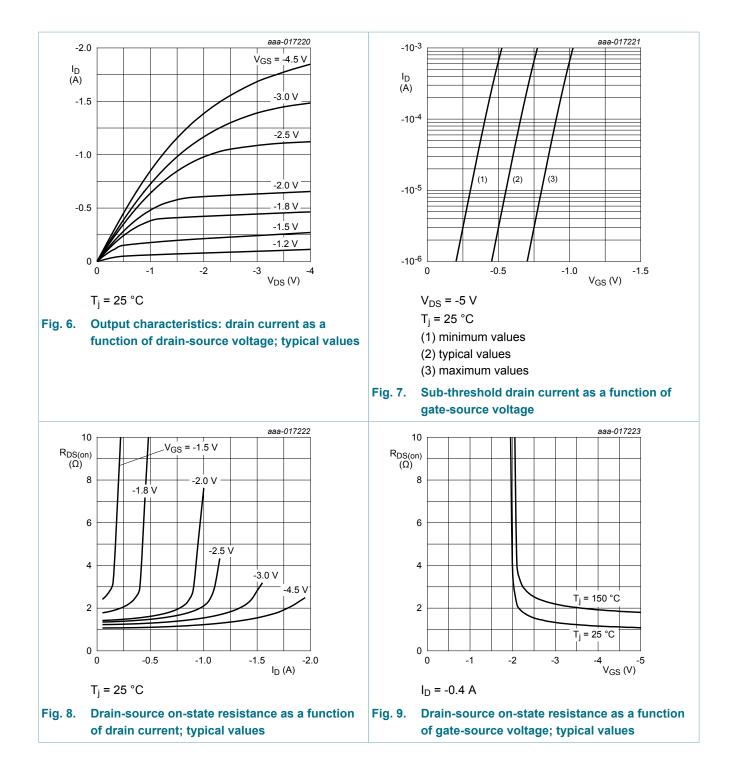
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	l				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		$V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-5	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		$V_{GS}$ = 2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 25 °C	-	1.2	1.4	Ω
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 150 °C	-	2	2.4	Ω
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -320 mA; T <sub>j</sub> = 25 °C	-	1.7	2.3	Ω
	V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -80 mA; T <sub>j</sub> = 25 °C	-	2.1	3.1	Ω	
		$V_{GS}$ = -1.5 V; I <sub>D</sub> = -10 mA; T <sub>j</sub> = 25 °C	-	3	5.1	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 25 °C	-	820	-	mS
Dynamic ch	naracteristics	· · · ·				
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -15 V; I <sub>D</sub> = -410 mA;	-	0.7	1.2	nC
Q <sub>GS</sub>	gate-source charge	$V_{GS} = -4.5 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$ - 0.2 -		-	nC	
Q <sub>GD</sub>	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -15 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	43.2	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	5.9	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4.2	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = -15 V; I <sub>D</sub> = -410 mA;	-	3	-	ns
t <sub>r</sub>	rise time	$V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ; $T_j$ = 25 °C	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	14	-	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-drai	in diode	1				
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -410 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.95	-1.2	V

PMZ1200UPE

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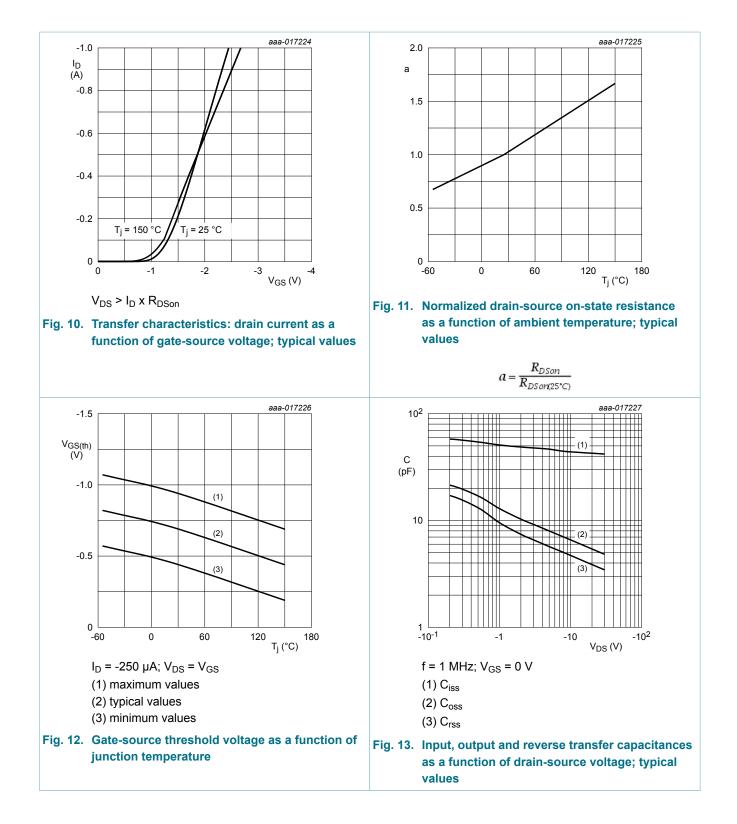
#### 30 V, P-channel Trench MOSFET



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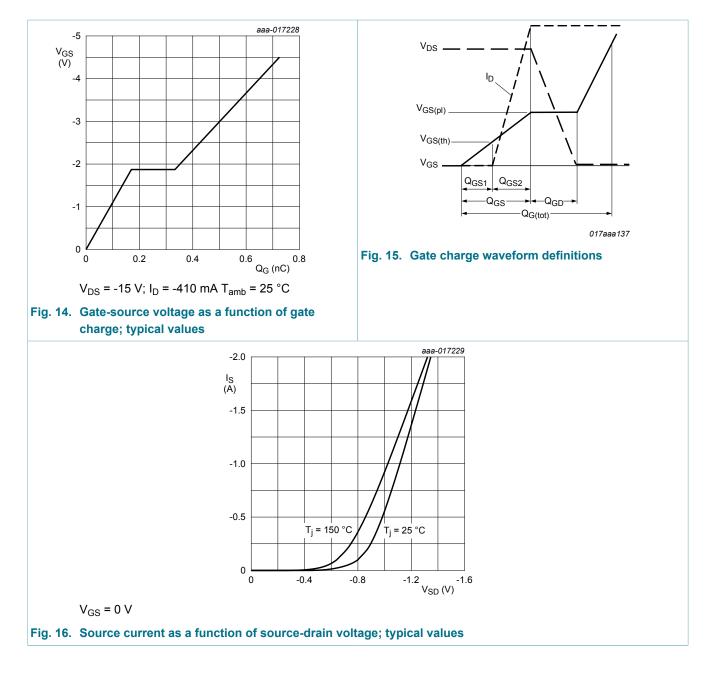


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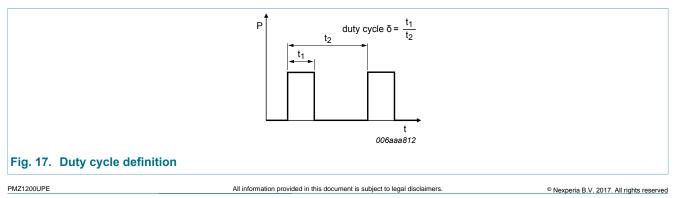
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#### 30 V, P-channel Trench MOSFET



# **11. Test information**



## **PMZ1200UPE**

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### 12. Package outline

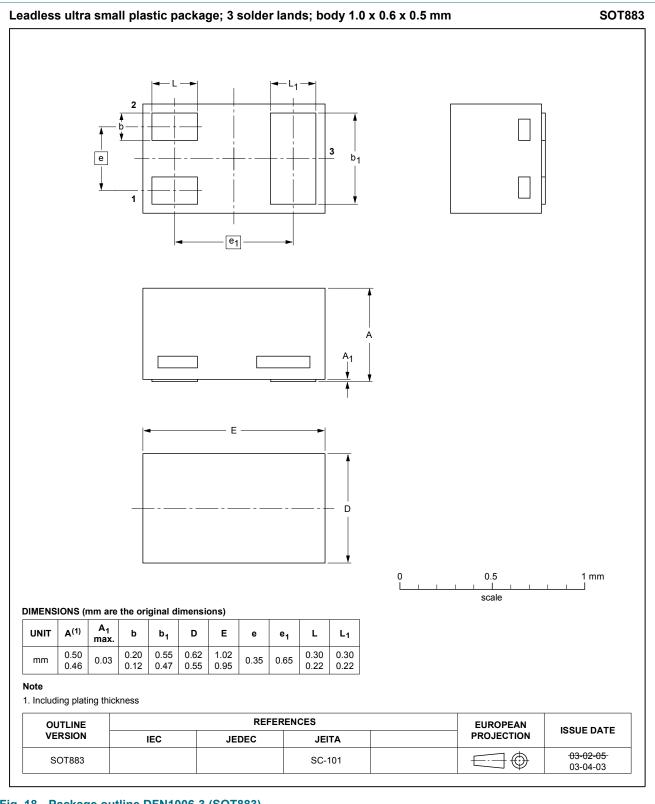


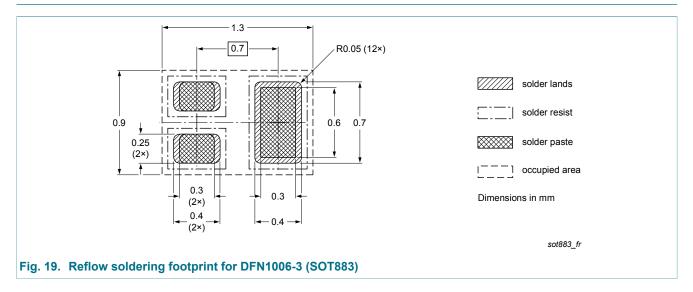
Fig. 18. Package outline DFN1006-3 (SOT883)
PMZ1200UPE All information

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# **PMZ1200UPE**

30 V, P-channel Trench MOSFET

### **13. Soldering**



### **PMZ1200UPE**

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# 14. Revision history

Table 8. Revision his	able 8. Revision history				
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMZ1200UPE v.1	20150325	Product data sheet	-	-	

### PMZ1200UPE

#### 30 V, P-channel Trench MOSFET

#### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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Product data sheet

### PMZ1200UPE

#### 30 V, P-channel Trench MOSFET

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#### 30 V, P-channel Trench MOSFET

### **16. Contents**

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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